

Application No. 10/781766
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YR
CLMPTO
Claims 1-6 (CANCELLED)

Claim 7 (original) A gallium nitride (GaN) based light-emitting device (LED), comprising:

a light-emitting body comprising a GaN-based material capable of emitting a light; and

a light extraction layer comprising:

a current spreading layer disposed over said light-emitting body; and
a micro-structure layer disposed over said current spreading layer
and being a Pt layer having metal clusters.

Claim 8 (original) The LED according to Claim 7, wherein said light-emitting body comprises an n-type GaN-based layer, a semiconductor active layer and a p-type GaN-based layer and said semiconductor active layer is disposed over said n-type GaN-based layer and said p-GaN-based layer is disposed over said active layer.

Claim 9 (original) The LED according to Claims 7 and 8, wherein said light-emitting body has a p-type electrode and an n-type electrode and said p-type electrode is disposed over said micro-structure layer.

Claim 10 (original) The LED according to Claim 9, wherein said p-type electrode is disposed beside said micro-structure layer and said current spreading layer.

Claim 11 (original) The LED according to Claim 6, wherein said current spreading layer is a transparent and conductive layer and selected from a group

consisting of a Ni/Au double layer structure, Ni, Pt, Pd, Rh, Ru, Os, Ir, Zn, In, Sn, Mg and an oxide thereof.

Claim 12 (original) The LED according to Claim 7, wherein said Pt layer having metal clusters is formed by annealing a Pt layer.

Claims 13-17 (canceled).

CLAIMS 18-25 (CANCELLED)